Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

3. Applications

- High-side loadswitch
- High-speed line driver
- Relay driver
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-3.5	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$		-	48	55	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1 2	G TITLE
			TO-236AB (SOT23)	S
				017aaa094

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV48XPA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV48XPA	%DZ

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-20	V	
V_{GS}	gate-source voltage			-12	12	V	
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.5	Α	
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.2	Α	
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW	
			[1]	-	930	mW	
		T _{sp} = 25 °C		-	4150	mW	
T _j	junction temperature			-	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain diode							
Is	source current	T _{amb} = 25 °C	[1]	-	-1	Α	

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

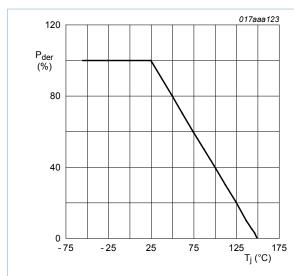


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

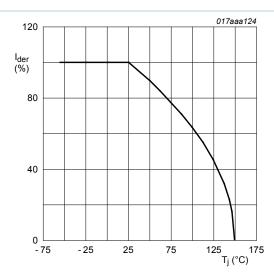


Fig. 2. Normalized continuous drain current as a function of junction temperature

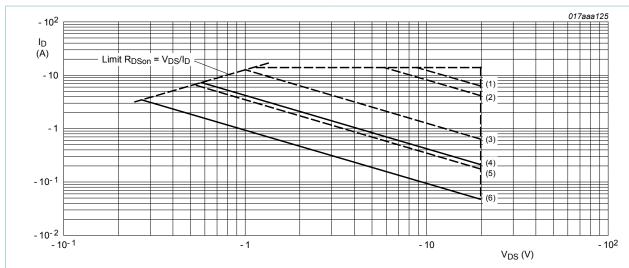
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMV48XPA

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I_{DM} = single pulse

- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; T_{sp} = 25 °C
- $(5) t_p = 100 ms$
- (6) DC; T_{amb} = 25 °C; drain mounting pad 6 cm²

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fi	thermal resistance from junction to ambient		[1]	-	213	245	K/W
			[2]	-	117	135	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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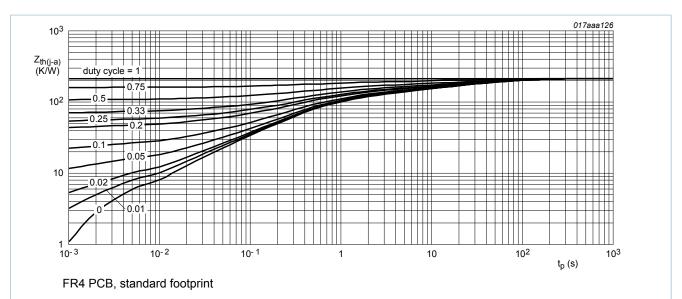


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

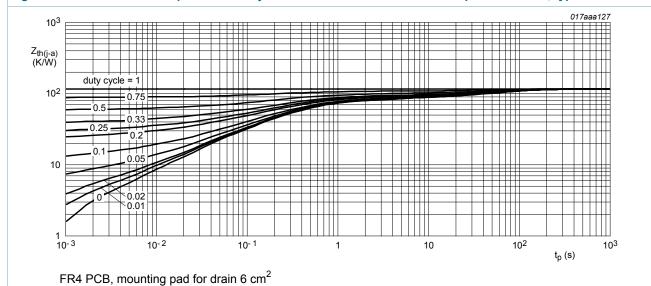


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _{amb} = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 °C	-	48	55	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 150 °C	-	70	80	mΩ
		V_{GS} = -2.5 V; I_D = -2 A; T_j = 25 °C	-	71	81	mΩ
9 _{fs}	forward transconductance	V_{DS} = -12 V; I_{D} = -2 A; T_{j} = 25 °C	-	12	-	S
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -1 A; V_{GS} = -4.5 V; T_{j} = 25 °C	-	8.5	11	nC
Q _{GS}	gate-source charge		-	1.8	-	nC
Q_{GD}	gate-drain charge		-	1.8	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	1000	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	130	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -1 A; V_{GS} = -4.5 V;	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	13	-	ns
t _{d(off)}	turn-off delay time		-	61	-	ns
t _f	fall time		-	23	-	ns
Source-dra	in diode		1			,
V _{SD}	source-drain voltage	I_S = -2.4 A; V_{GS} = 0 V; T_j = 25 °C	-	-0.82	-1.2	V

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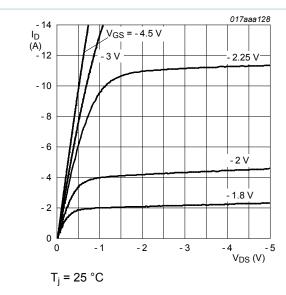
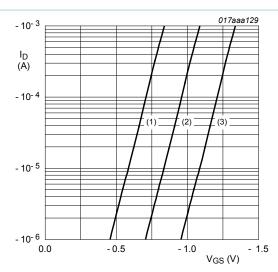


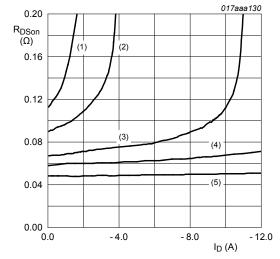
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -3 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



$$T_i = 25 \,^{\circ}C$$

$$(1) V_{GS} = -1.8 V$$

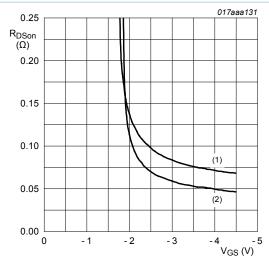
(2)
$$V_{GS} = -2.0 \text{ V}$$

$$(3) V_{GS} = -2.25 V$$

$$(4) V_{GS} = -3.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



$$I_D = -2.4 A$$

(1)
$$T_i = 125 \, ^{\circ}C$$

(2)
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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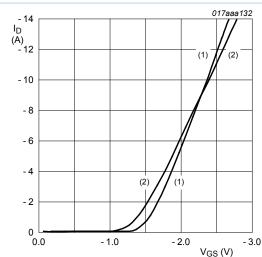
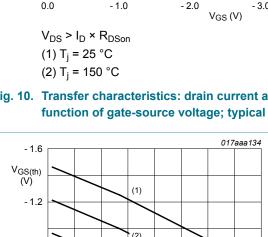


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



(3)

 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values

-0.8

- 0.4

0.0

- 60

(3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

T_i (°C)

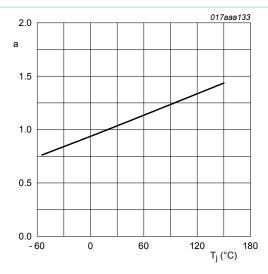
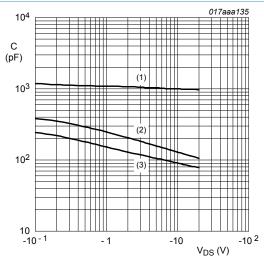


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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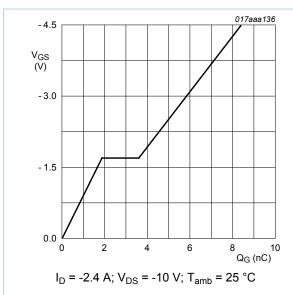


Fig. 14. Gate-source voltage as a function of gate charge; typical values

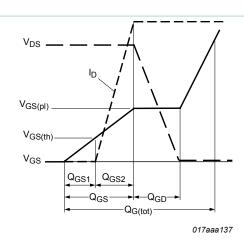
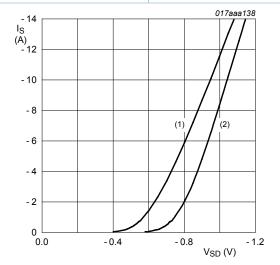


Fig. 15. Gate charge waveform definitions



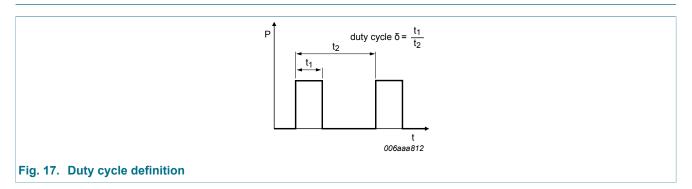
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$

(2) $T_i = 25 \,^{\circ}\text{C}$

Fig. 16. Source current as a function of source-drain voltage; typical values

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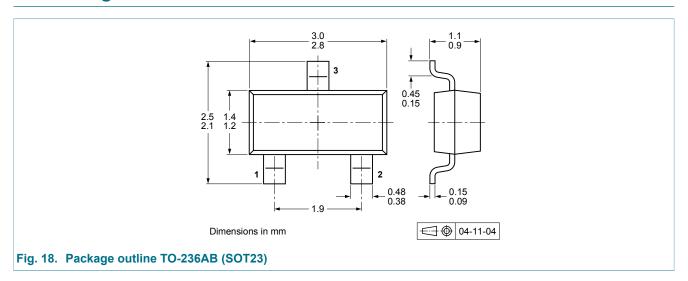
11. Test information



11.1 Quality information

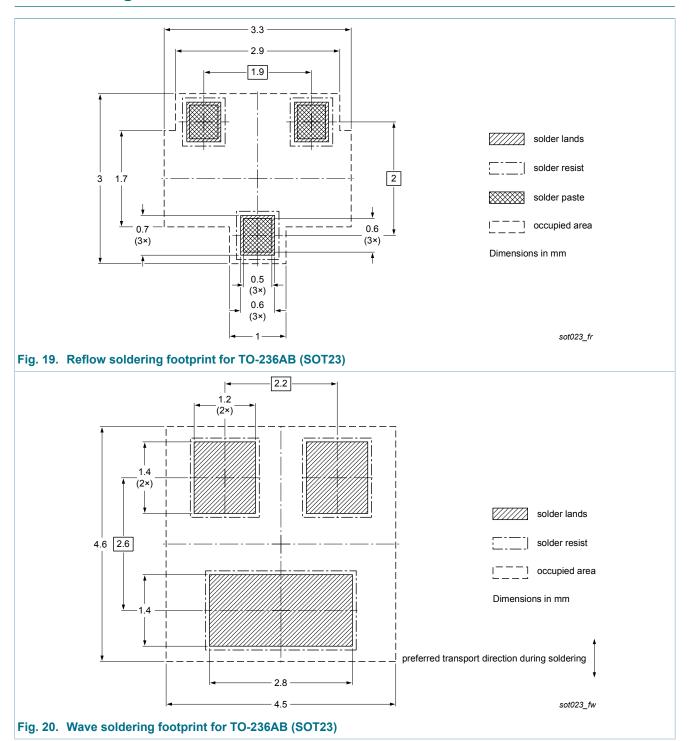
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV48XPA v.1	20140310	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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